Electronic Services - Los Angeles
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Instruction Manual
Models GS-3, GP-4

TRANSISTOR TEST SETS

Baird-Atomic, Inc.

33 UNIVERSITY ROAD • CAMBRIDGE 38, MASS.

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TABLE 2-1

SMALL SIGNAL COEFFICIENTS MEASURED DIRECTLY

		Coefficients for All Frequencies		Coefficients for Low Frequencies				
	Multiplier	Hybrid	Other Names	Hybrid	Other Names	Equivalent T	Good Approx for Junctions	Measured at 159kc
GROUNDED BASE	100 ohms	h_{ib}	$\frac{1}{y_{11_b}}$		$\frac{1}{g_{11_b}}$	$r_e+r_b(1-\alpha)$		
	1.0	$-h_{fb}$	α		α	α	α	
	1.0	h_{fb}	$1-\alpha$				$1-\alpha$	
	0.1			$1+h_{fb}$		$1-\alpha$	$1-\alpha$	
	0.001	h_{rb}	γ_b		γ_b			
	10 μmhos	h_{ob}	$\frac{1}{z_{22_b}}$					C_c
	1 μmho			h_{ob}	$\frac{1}{r_{22_b}}$	$\frac{1}{r_c+r_b}$	$\frac{1}{r_c}$	
	1000 ohms			$\frac{h_{rb}}{h_{ob}}$	r_{12_b}	r_b		
	1 meg			$\frac{1}{h_{ob}}$	r_{22_b}	r_c+r_b	r_c	
GROUNDED EMITTER	100 ohms			h_{ie}	$\frac{1}{g_{11_e}}$		$r_b+\frac{r_e}{1-\alpha}$	
	1	h_{fe}	β			$\frac{\alpha}{1-\alpha}$		
	0.001			h_{re}	γ_e			
	10 μmhos	h_{oe}	$\frac{1}{z_{22_e}}$					
	1 μmho							
	1000 ohms			$10\frac{h_{re}}{h_{oe}}$	$10r_{12_e}$	$10r_e$		
	1 meg			$10\frac{1}{h_{oe}}$	$10r_{22_e}$	$10\times r_c(1-\alpha)+r_e$	$10\times r_c(1-\alpha)$	

TABLE 2-2

RANGE OF PARAMETERS AND ACCURACY, NOMINAL LIMITS
(Exclusive of VTVM Errors)

Parameter	X	Measurable Range	Low-Frequency Accuracy	High-Frequency Accuracy	Limitations For Stated Accuracy
h_{ib}	x100	10 to 1000 ohms	3% to 500 kc	5% to 1 mc	
$-h_{fb}$	x1.0	0.1 to 10	3% to 1 mc	3% to 1 mc	h_{ib} < 1000 ohms
$1+h_{fb}$	x1.0	0.1 to 1	3% to 500 kc	5% to 1 mc	h_{ib} < 1000 ohms
$1+h_{fb}$	x0.1	0.01 to 0.1	3% to 100 kc	5% to 300 kc	h_{ib} < 1000 ohms
h_{rb}	x0.001	0.0001 to 1.0	3% to 500 kc	5% to 1 mc	h_{ib} < 500 ohms
h_{ob}	x10	1 to 1000 μmhos	3% to 500 kc	5% to 1 mc	r_b < 1000 ohms
h_{ob}	x1	0.1 to 10 μmhos	3% to 100 kc	5% to 300 kc	r_b < 1000 ohms
r_b	x1000	100 to 5000 ohms	3% to 100 kc	5% to 300 kc	r_c > 100 K ohms
r_c+r_b		0.1 to 10 meg	3% to 100 kc	5% to 300 kc	r_b < 1000 ohms
h_{ie}		10 to 3000 ohms	5% to 50 kc		
$+h_{fe}$		1 to 1000	5% to 1 mc	5% to 1 mc	h_{ie} < 3000 ohms
h_{re}		0.0001 to 1.0	5% to 50 kc		h_{ie} < 3000 ohms
h_{oe}	x10	1 to 300 μmhos	5% to 500 kc		h_{oe} < 300 > μmhos βr_e < 3000 ohms
r_e		10 to 1000 ohms	5% to 100 kc		r_b < 3000 ohms h_{ie} < 3000 ohms
r_{22e}		10K to 1 meg	5% to 500 kc		r_{22e} > 3000 ohms βr_e < 3000 ohms

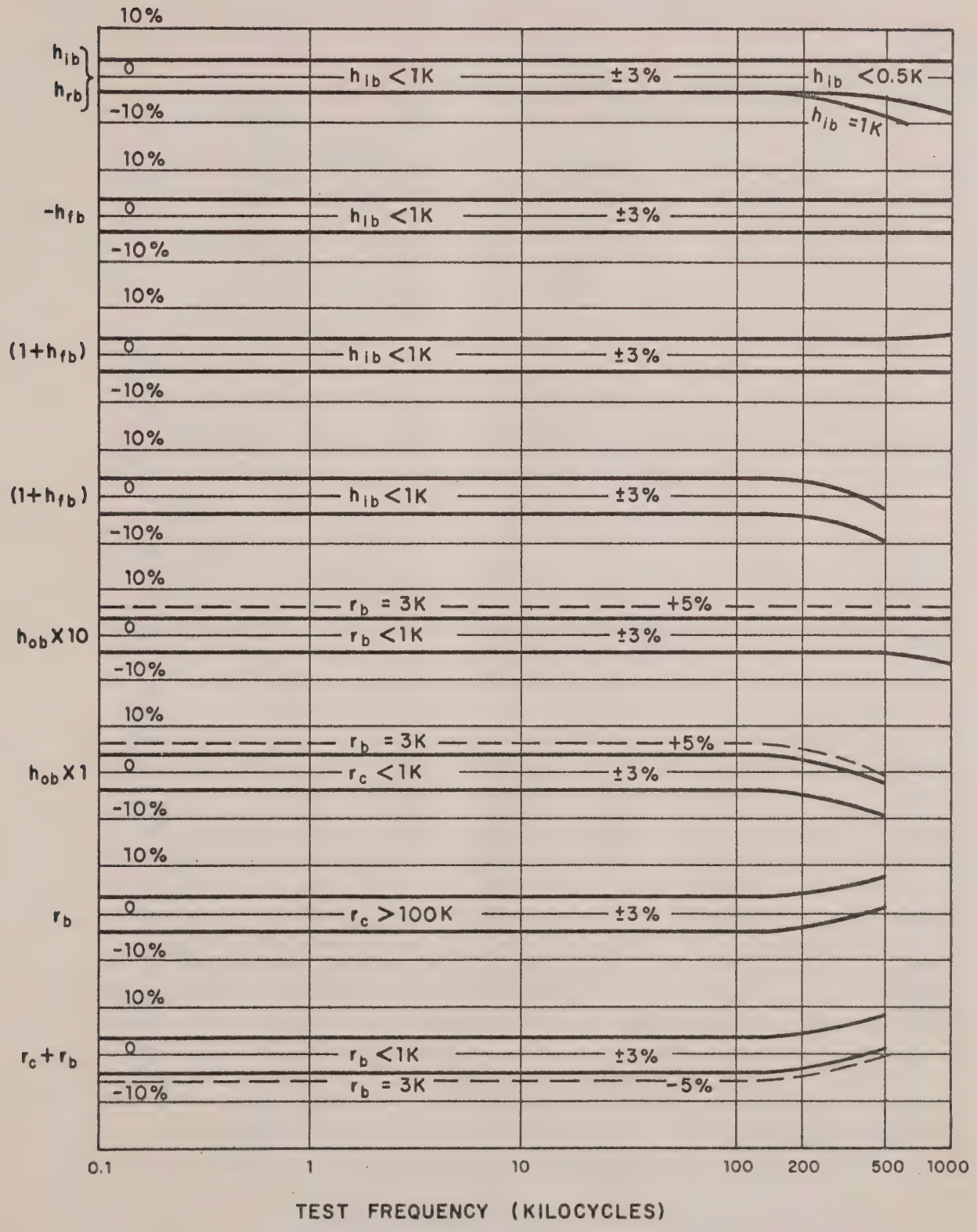


Figure 2-1. Accuracy vs. Frequency, Grounded Base Parameters

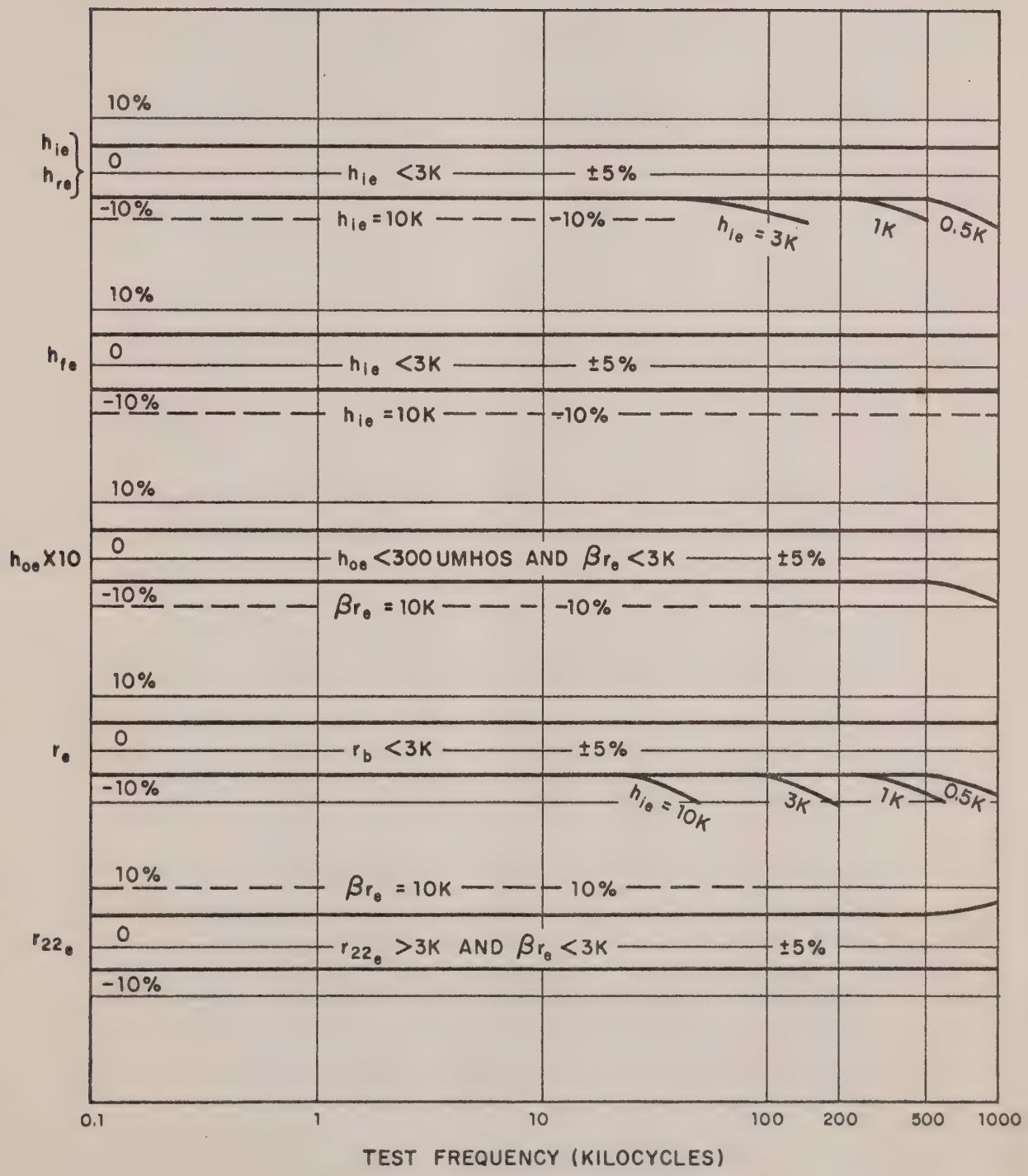


Figure 2-2. Accuracy vs. Frequency, Grounded Emitter Parameters

The following adaptors are also available:

Model HL General Purpose Adaptor with low capacity spring clips for transistors with long leads.

Model HM Texas Instruments Junction Tetrodes

Model ND For long lead transistors

Other Adaptors are available on special order to take specified transistor types.

Note: The General Radio Type 561-415-2 spring clip adaptor may be used in the Transistor Test Set without modification (for low frequency tests only).

2-9. ACCESSORY EQUIPMENT REQUIRED

Oscillator:

Output up to 10 volts should be available (no load).

Output impedance 600 ohms or less recommended. (Higher values are permissible but operation may be less convenient.)

Frequency range to cover tests desired or 100 cps to 1 mc.

Vacuum-Tube Voltmeter:

Sensitivity 0.001 volt full scale with other ranges in decades up to 10 volts full scale.

Input impedance at least 0.5 megohm shunted by not more than 25 μμf for tests at 1 mc. For lower frequencies proportionally more capacitance can be tolerated.

2-10. OPTIONAL ACCESSORY EQUIPMENT FOR SPECIAL TESTS

Cathode Ray Oscilloscope:

Useful for monitoring transistor output signal for distortion or noise in cases of unusual bias conditions or high-noise transistors.

2-11. MODELS AVAILABLE

GP-4 -- Standard Cabinet Model

GS-3 -- Rack Mounting Model

2-12. POWER SUPPLY

Models GS-3 and GP-4 -- Four 45V Batteries, Burgess Type 5308 or equivalent. (Probable life in normal use 3 to 6 months or more.)

2-13. OVERALL DIMENSIONS

Model GP-4 -- 22" long x 13" high x 10" deep, maximum.

Model GS-3 -- Panel 19" x 10-1/2", depth 9", maximum.

2-14. WEIGHT

Model GP-4 -- 40 lbs. net. Shipping weight 70 lbs.

Model GS-3 -- 30 lbs. net. Shipping weight 60 lbs.

SECTION 3
OPERATION

3-1. UNPACKING AND SETTING UP

The battery compartment is accessible in the Model GP-4 by unscrewing the rear panel, and in the Model GS-3 by means of the hinged door in the rear.

Check terminals of batteries to see that they have not loosened during shipment.

An oscillator (not supplied, see paragraph 2-9) should be connected to the OSC IN terminals (the black terminal is the grounded terminal).

A vacuum tube voltmeter (not supplied, see paragraph 2-9) should be connected to the AC VTVM connector with the coaxial cable provided.

3-2. EXPLANATION OF PANEL CONTROLS

NPN-PNP (S1)

Polarity-reversing switch for bias.

For point-contact transistors, set to PNP position.

GROUNDED EMITTER - GROUNDED BASE (S3)

Switches transistor configuration to either grounded base (for h_{ib}, h_{rb}, etc.) or grounded emitter (for h_{ie}, h_{re}, etc.).

BIAS ON - OFF I_{co} (S2)

In OFF position, biases are removed from transistor socket and battery drain is zero. In BIAS ON, biases are applied to transistor (even if meter is not indicating). In I_{co} the collector has voltage applied but the emitter is open.

HIGH - LOW (S12)

Reduces voltage from OSC in LOW position, for fine control in setting of E_R.

BIAS METER (M1)

Indicates d-c bias voltage and currents and their polarity when proper lever switch is pushed.

EXTERNAL BIAS METER JACK (J2)

A phone plug connected to a meter or galvanometer plugged in here automatically disconnects the BIAS meter and inserts the external meter for measuring I_{co} below 2 microamperes.

I_e ADJUST (R5)

Sets I_e to desired value in conjunction with lever switches and BIAS meter in grounded base configuration.

I_b ADJUST (R10)

Sets I_b to obtain desired I_c in grounded emitter configuration.

V_c ADJUST (R9)

Control for setting V_c to desired value.

PUSH TO READ BIAS (S6 to S11)

Six spring-return lever switches used singly in conjunction with the BIAS meter to select meter range and to indicate bias voltage or current. In the center or neutral positions the BIAS meter is out of the transistor circuit but the biases are still applied. When a key is depressed the existing bias is indicated on the meter and may be varied by the I_1 or V_1 ADJUST controls.

Note: I_e is the d-c emitter current in grounded base
I_b is the d-c base current in grounded emitter
V_e is the d-c emitter to base voltage in grounded base
V_b is the d-c base to emitter voltage in grounded emitter
I_c is the d-c collector current
V_c is the d-c collector voltage

COEFFICIENT SELECTOR (S5)

Selects the desired coefficient in conjunction with the GROUNDED EMITTER-GROUNDED BASE switch. The latter determines whether the coefficient will be read on the GROUNDED EMITTER ring or on the GROUNDED BASE ring.

For coefficients on the HYBRID ring, the GROUNDED EMITTER - GROUNDED BASE switch adds, in effect, the subscript e or b to the indicated h-parameter. (See table 2-1.) Hence, this ring gives two complete series of h-coefficients. A few less-used coefficients not marked on the panel are also obtainable by direct reading as shown in table 2-1. Simply set selector to a corresponding parameter shown in the same horizontal row of table 2-1.

The outer ring indicates the multiplying factor used in conjunction with the VTVM reading, E_X.

The rectangle around the coefficient h_{ie}, $1+h_f$, h_r, h_f, and h_o indicates roughly that these are the coefficients which can be read to 1 mc, whereas the others have individual frequency limits. (See table 2-2.)

ER-EX (S4)

In the center position the circuit is set for adjusting the oscillator signal level to the reference value E_R, usually 1 millivolt on the external vacuum tube voltmeter.

In the down position the circuit is set for reading the value of the coefficient (called E_X before decimal point and dimensional units have been determined) on the vacuum tube voltmeter.

TRANSISTOR ADAPTOR SOCKET

The adaptor plugs into this octal socket on the panel.

SECTION 4

STEP-BY-STEP MEASUREMENT PROCEDURE

4-1. MEASUREMENT OF A-C COEFFICIENTS

a. Plug proper adaptor into octal socket.

b. Check to see that BIAS ON switch is in OFF position.

CAUTION: Always have this switch OFF while inserting or removing transistors. Failure to do so may damage the transistor.

c. Plug transistor into socket.

d. Set NPN-PNP switch to required position. (Refer to the manufacturer's data.)

e. Set GROUNDED EMITTER-GROUNDED BASE switch to configuration required depending on coefficients desired. (See table 2-1.)

f. Turn BIAS ON-OFF switch to BIAS ON position.

g. Set d-c bias currents as follows:

1. For grounded base connection:

(a) Set emitter current to desired value by I_e ADJUST control while pushing proper I_e lever switch to indicate current on BIAS meter. Then release I_e switch.

CAUTION: Avoid depressing red I_e or I_c lever switches to 50 μa position accidentally or unless it is known that current will be within 50 μa range. Damage to meter may result.

(b) Set collector voltage to desired value by V_c ADJUST control while pushing V_c lever switch to the appropriate range to indicate voltage on BIAS meter. Then release V_c switch and the biasing is complete.

(c) V_e may now be read, if desired, using V_e switch.

2. For grounded emitter connection:

(a) Check to be sure that the COEFFICIENT SELECTOR is not in either the $(1+h_f) \times 0.1$ or the $h_o \times 1$ position which are blank in the GROUNDED EMITTER ring of the dial.

(b) Set up desired I_e and V_c in GROUNDED BASE configuration. Turn up I_b control.

Note: The V_c supply is not a constant voltage supply. If the transistor is switched to grounded emitter and the I_b control is CCW, V_c will increase, since no current is drawn from the supply. With the I_b control turned up, current is being drawn from the V_c supply at the moment of switching, thus keeping V_c down to safe levels. This note is especially applicable to surface barrier transistors.

(c) Observe I_c by pressing appropriate I_c lever switch.

(d) Switch to GROUNDED EMITTER.

(e) Using I_b ADJUST control while depressing I_c lever switch, readjust I_c to value observed under step (c).

(f) The biasing is now complete and the transistor may be switched from GROUNDED EMITTER to GROUNDED BASE or back again to GROUNDED EMITTER without changing bias conditions.

(g) The base current, I_b, may now be measured, if desired, using the red I_b switch.

(h) The base voltage, V_b, may be read, using the V_b switch.

Note: If transistor is being operated near its maximum rated dissipation, the biases can be expected to drift due to internal heating in the transistor until equilibrium is reached. This is especially true in case of grounded emitter operation and may necessitate a reduction of power input to obtain reproducible readings.

h. Set COEFFICIENT SELECTOR to desired position. (See table 2-1 for additional coefficients not listed on dial.)

i. Set external oscillator to desired frequency.

j. Adjust amplitude of oscillator signal (by oscillator's output control) until external VTVM reading is 1 millivolt, with the E_R-E_X switch in the E_R or center position. Use the LOW position of the HIGH-LOW switch if amplitude control on oscillator is too coarse at low end.

k. Depress the E_R - E_X switch to E_X position and read E_X in millivolts on the VTVM. If necessary to switch VTVM to a different scale, make the proper decimal point correction.

l. Divide E_X (in millivolts) by E_R (in millivolts), giving E_X/E_R the magnitude of the desired coefficient, without its units.

m. Multiply E_X/E_R by the figure in the outer ring of the COEFFICIENT SELECTOR dial, giving the value of the coefficient together with its units. (Note that h_f, α, β, $1+h_f$ and h_r are dimensionless.)

4-2. EXAMPLE OF MEASUREMENT OF A COEFFICIENT

Let us say the coefficient to be measured is $1 - \alpha$.

a. Set the COEFFICIENT SELECTOR to the $1 - \alpha$ position which has 0.1 in the outer ring (for low frequencies).

b. With E_R-E_X switch in E_R position, set oscillator level until the VTVM reads 1 millivolt (full scale).

c. Depress the switch to E_X position.

d. Read 0.45 millivolt on the same scale.

e. Hence $E_X/E_R = 9,45/1 = 0.45$.

f. Multiply by the outer ring multiplying factor which is 0.1, giving 0.045 for $1 - \alpha$. Hence $\alpha = 0.955$.

4-3. SPECIAL NOTES

a. h_f or α

The direct measurement of α in this position will be accurate to approximately 3 percent. For more accurate values of α use the $(1+h_f) \times 0.1$ position, giving 0.3 percent accuracy.

b. $1+h_f$ or $1 - \alpha$

The x 0.1 position is generally used at low frequencies and for values of α between 0.90 and 0.99 and the x 1 position for α less than 0.90. The x 0.1 position is not used in grounded emitter.

c. h_o

The x 1 position is generally used at low frequencies and for values of h_{22} between 0.1 and 2 μmhos and the x 10 position for high frequencies or for point-contact transistors. The x 1 position is not used in grounded emitter.

d. r_e, r_b, $r_c + r_b$

It will be necessary to readjust the oscillator amplitude for each of these positions and for each transistor. For r_e, switching over to GROUNDED EMITTER will necessitate re-establishing the d-c biases. (See subparagraph 4-1g2.) The quantity read directly in the r_e position is actually 10 r_e, as shown on the dial, so the reading must be divided by 10 in addition to multiplying by 1000 ohms. In other words, the multiplier for r_e is 100 ohms. With junction transistors, r_c+r_b will be equal to r_c to better than 1 percent accuracy since $r_b << r_c$.

e. Distortion

The peak-to-peak signal swing in the collector circuit should not be allowed to exceed the d-c bias voltage on the collector or distortion and consequent inaccurate reading will result. With the great majority of transistors, the recommended reference voltage of 1 millivolt will not result in distortion unless the d-c collector voltage is less than 3 volts, except in measuring r_b or $r_c + r_b$. For these coefficients, the collector voltage should always be maintained at a voltage no less than 3 times r_c (where r_c is in megohms). Alternatively, E_R may be reduced to the point where distortion does not occur as seen by an oscilloscope monitoring the VTVM output. Parameter reading must then be divided by the same factor by which E_R was reduced below the standard value of 1 millivolt.

f. Noise

If readings are suspected of being inaccurate due to high noise, check by turning off signal. If reading does not drop 10 to 1, a higher value of E_R should be used, and the readings corrected accordingly.

4-4. MEASUREMENT OF COLLECTOR CAPACITANCE, C_c

Direct reading may be obtained on the VTVM dial as follows:

a. Follow procedure of paragraph 4-1, steps a through b, as usual, using GROUNDED BASE configuration.

b. Set oscillator frequency to 159 kc.

c. Set the COEFFICIENT SELECTOR TO C_c (same as h_o x 10).

d. Set VTVM, E_R, to 1 millivolt.

e. Depress E_R-E_X switch to E_X and read collector capacitance on VTVM, reading μμf in place of μmhos for units.

f. Check to see if true capacitance is being measured by dropping frequency to some low value, say 100 to 1000 cycles. If h_o goes down 4 times or more in value, (as it will with most transistors) the capacitance measured was accurate.

NOTE: The adaptor is specially designed for low capacitance. The stray capacitance between collector and base at the transistor socket is approximately 0.1 μμf.

4-5. MEASUREMENT OF ALPHA CUTOFF, $f_{\alpha o}$ AND BETA CUTOFF $f_{\beta o}$

a. Measure α or β at low frequency in usual way, using the h_f position.

b. Increase frequency until α or β drops 3 db or to 0.707 times its low frequency value.

c. Read $f_{\alpha o}$ or $f_{\beta o}$ on oscillator frequency dial.

4-6. MEASUREMENT OF I_{co} (COLLECTOR CUTOFF CURRENT, I_c WITH $I_e = 0$)

a. Follow steps a through d in paragraph 4-1.

b. Set to GROUNDED BASE configuration.

c. With no oscillator input to the Transistor Test Set, turn BIAS ON-OFF-I_{co} switch to I_{co}.

d. Adjust V_c to desired voltage while depressing V_c lever switch.

e. Throw red I_c switch first to 500 μa, then to 50 μa, and read I_{co} on BIAS meter.

f. An external sensitive microammeter or galvanometer may be plugged into the EXTERNAL BIAS METER jack to read I_{co} below 2 microamperes. Use a 2-wire phone plug wired to the external meter. Use the 50 μa position of I_c which removes all shunts.

4-7. MEASUREMENT OF V_{ch} (CHANNEL EFFECT VOLTAGE, V_e WITH $I_e = 0$)

a. Follow steps a through d, paragraph 4-1.

b. Set to GROUNDED BASE configuration.

c. Turn BIAS ON-OFF-I_{co} switch to I_{co}.

d. Adjust V_c to desired voltage while depressing V_c lever switch.

e. Depress V_e lever switch and read V_{ch} on BIAS meter.

TABLE 4-1

TYPICAL VALUES OF LOW FREQUENCY PARAMETERS FOR JUNCTION TRANSISTORS (FOR BIAS OF I_e = 1 MA, V_c = 5 VOLTS)

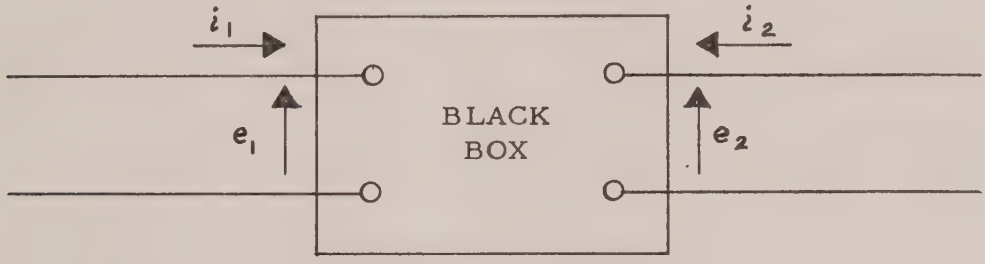
h_{ib}	25 to 100 ohms	r_b	100 to 1000 ohms
$-h_{fb}$	0.90 to 0.99	r_e	10 to 50 ohms
$1+h_{fb}$	0.01 to 0.10	r_c	0.5 to 5 meg
h_{rb}	0.0001 to 0.001		
h_{ob}	0.2 to 2.0 μmhos	C_c C_{ob}	10 to 50 μμf
h_{ie}	500 to 3000 ohms	$f_{\alpha o}$	0.5 to 5 mc
h_{fe}	10 to 100		
h_{re}	0.0005 to 0.010	I_{co}	1 to 15 μa
h_{oe}	5 to 100 μmhos	V_{ch}	0.01 to 0.30 volts

SECTION 5

THEORY OF OPERATION

5-1. HYBRID PARAMETERS

5-2. It may be shown[1] that a transistor operating linearly under small signal conditions may be represented by a 4-terminal network element or "black box".



The changes of voltage and current about a given operating point or set of d-c biases may be represented in various ways using open or short-circuited impedances or admittance parameters. From the point of view of measurability, a set of parameters involving a combination of both open-circuited and short-circuited conditions, called "hybrid" parameters[2], has been found useful in junction transisto analysis.

5-3. The hybrids are defined as the coefficients in the following equations for the "black box" above

$$e_1 = h_i i_1 + h_r e_2$$

$$i_2 = h_f i_1 + h_o e_2$$

---

[1] "Transistor Audio Amplifiers," by R. F. Shea, John Wiley and Sons, 1955.
[2] "Communication Networks," 2nd Edition, by E. A. Guillemin, John Wiley and Sons, 1952.

From these equations it is seen, by successively setting e_2 and i_1 equal to zero (that is, an a-c short-circuited output and an a-c open-circuited input respectively) in each equation, that

$$h_i = \left.\frac{e_1}{i_1}\right| \quad e_2 = 0 \quad = \text{input impedance with output short-circuited}$$

$$h_r = \left.\frac{e_1}{e_2}\right| \quad 1 = 0 \quad = \text{voltage feedback ratio with input open-circuited}$$

$$h_f = \left.\frac{i_2}{i_1}\right| \quad e_2 = 0 \quad = \text{current amplification with output short-circuited}$$

$$h_o = \left.\frac{i_2}{e_2}\right| \quad i_1 = 0 \quad = \text{output admittance with input open-circuited}$$

It is upon the above definitions that the principle of operation of the Baird-Atomic Transistor Test Set is based.

5-4. It follows that there are two complete sets of these hybrid parameters depending upon whether the transistor is connected in grounded-base or grounded-emitter configuration. The subscripts"b" and "e" are used with the h-parameters to define this configuration.

5-5. A chart showing simplified circuits of the ones used for measuring the parameters is given in figure 5-1 in order to clarify the theory of operation of the Transistor Test Set. (Blocking condensers, d-c bias supplies, and bias metering circuits are omitted for simplicity.) It will be seen that the circuits closely follow the definitions of the h-parameters as stated in paragraph 5-3. The 100K/100 ohm voltage dividers allow setting of a 1-volt signal level using the 0.001 volt scale of the vacuum tube voltmeter, thus minimizing the amount of decade switching between the setting of E_R and the measuring of E_X.

A fifth hybrid parameter, $1 + h_f$, is added to increase the accuracy of determination of h_f. The quantity $1 + h_f$ (or $1 - \alpha$) also appears frequently in equivalent

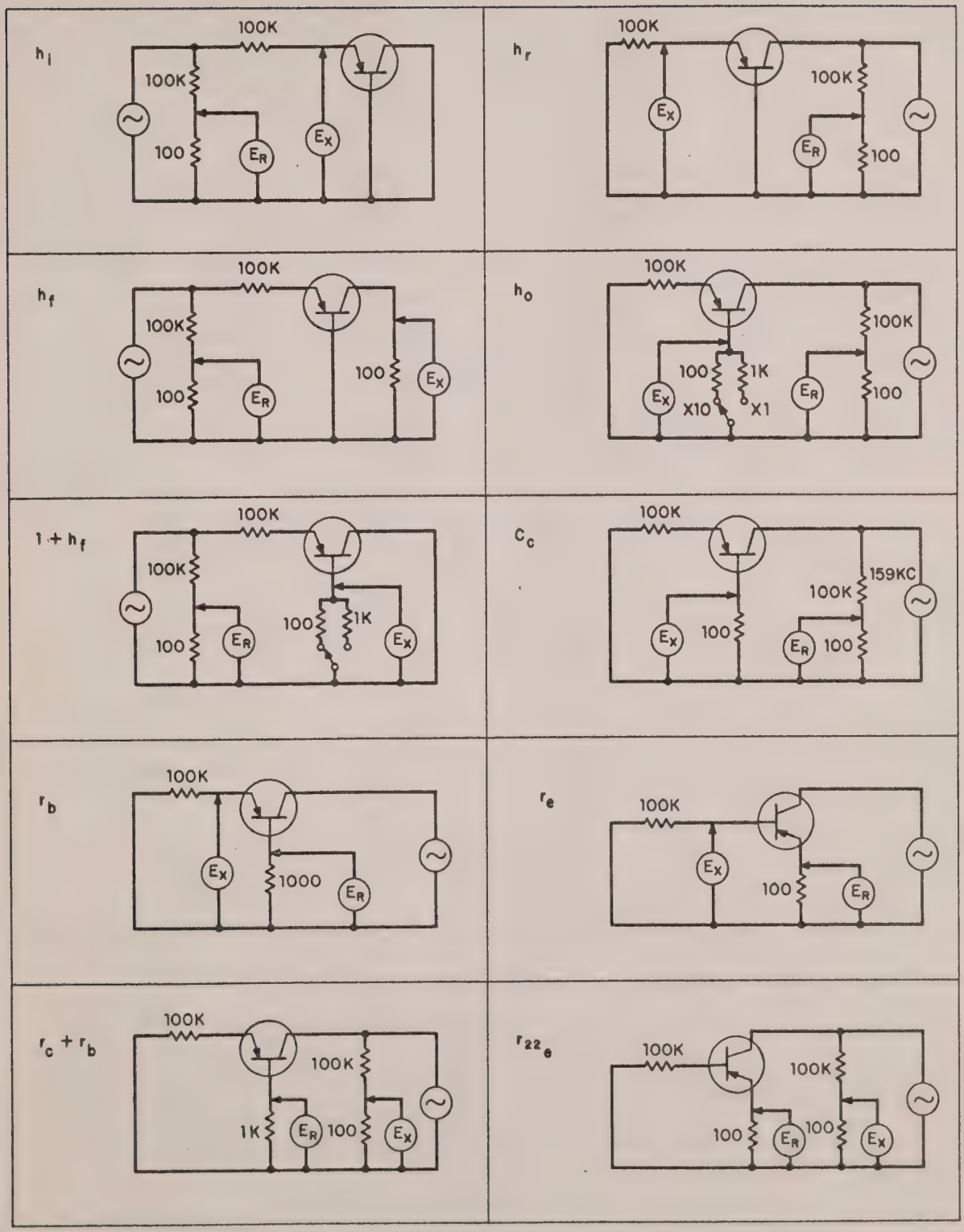


Figure 5-1. Simplified Measuring Circuits of the Transistor Test Set

circuit computations. If h_f (or - α) is greater than 0.9, the accuracy with which it may be measured is more than 10 times greater using the quantity $1 + h_f$ as the directly measured parameter.

For h_i, h_f, and $1 + h_f$, the input signal is 10 microamperes. For h_r and h_o the applied signal is 1 volt. These values are suitable for most transistors, but if unusually low values of bias are used, distortion may result and the reference E_R will have to be reduced. (See subparagraph 4-3 e.) On the other hand, to measure transistors having h_f greater than 0.99 in the $(1 + h_f) \times 0.1$ position, the reference may be increased in order to get a reading of E_X.

5-6. In table 2-1 are shown equivalent names[3] for the hybrid parameters, for example:

$$h_{ib} = \frac{1}{Y_{11b}} = \text{(for low frequencies)} \quad \frac{1}{g11_b}$$

$$h_{rb} = \gamma b$$

$$-h_{fb} = \alpha \qquad +h_{fe} = \beta$$

$$1+h_{fb} = 1 - \alpha$$

$$h_{ob} = \frac{1}{z_{22}{}^b} = \text{(for low frequencies)} \quad \frac{1}{r_{22_b}}$$

5-7. EQUIVALENT T CIRCUIT PARAMETERS

5-8. One of the most common equivalent circuits of a transistor is that using the current generator representation shown below[4]:

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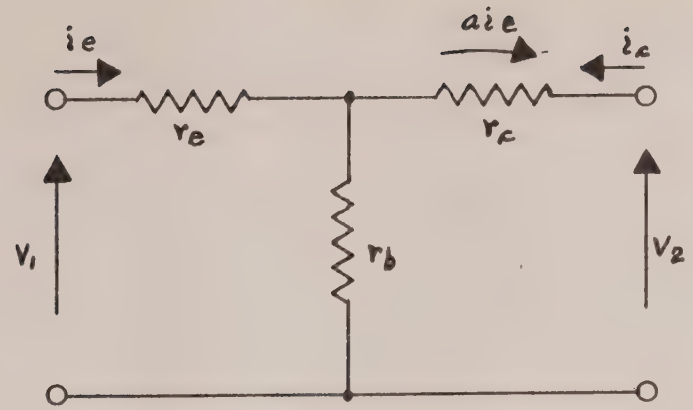
[3] Knight, Johnson and Holt, "Measurement of the Small-Signal Parameters of Transistors," Proc. I.R.E., Vol. 41, No. 8, p. 984, August, 1953.

[4] "Transistor Audio Amplifiers," by R.F. Shea, John Wiley and Sons, 1955, Chap. 2.



5-9. The quantities r_e, r_b and $r_c + r_b$ can be measured directly on the Transistor Test Set as shown in table 2-1. Since for junction transistors r_b is less than one thousandth of r_c, the latter may be read directly with good accuracy.

5-10. The simplified measuring circuits for these parameters are shown in figure 5-1. For r_b and r_c, a reference current of 1 microampere is used in the collector circuit, and for r_e it is 10 microamperes. If excessive noise is present, errors in readings may result. Within the limitations imposed by collector circuits, distortion, the reference signal E_R may then be increased and the readings compensated proportionately (see paragraph 4-3 e).

5-11. OTHER A-C PARAMETERS

5-12. Collector capacitance, C_c, the effective capacitance between collector and base of the transistor, is measured directly in the h_{ob} x 10 position, using f = 159 kc. The open-circuited output admittance assuming C_c in parallel with r_{22} is

$$h_o = \frac{1}{r_{22}} + i^{\omega C}$$

At frequencies high enough such that

$$\omega C_c >> \frac{1}{r_{22}}, \quad h_o = \omega C_c$$

If f = 159000 cps, $\omega = 10^6$

then $h_o = C_c \times 10^6 = C_c$ ($\mu\mu$f)

or the magnitude of h_o as read will be equal to the capacitance. (The multiplier x 10 still applies, so the reading will be x 10 $\mu\mu$f.) Neglecting $1/r_{22}$ will cause less than 5 percent error in C_c provided r_{22} (in megohms) x C_c (in $\mu\mu$f) is greater than 3.

5-13. The low-frequency parameters r_{12b} and r_{12e} are equal to r_b and r_e respectively and so are directly measurable. Similarly $r_{22b} = r_c + r_b$, and in the corresponding grounded emitter position r_{22e} may be read directly. The other r-parameters r_{11} and r_{12} may be easily computed.

GP-4 PARTS LIST

Ref. Number	Part Name and Description	B/A No.
B1, B2	Battery, 45V	00459
C1, C2, C3	Capacitor, 1.0 μfd, 200V, Mylar	00617
C4, C6	Capacitor, 2.0 μfd, 200V, Mylar	00666
C5	Capacitor, 0.1 μfd, 200V, Mylar	00583
J1	Connector, receptacle	00702
J2	Connector, phone jack	00777
J3	Binding post, red	01334
J4	Binding post, black	01337
L1	Choke, 22 μh	00891
P1	Connector, plug	00874
	Connector, cable adaptor	00876
R1, R2, R6	Resistor, 100K, 1/2W, 1%	01143
R3, R7, R11	Resistor, 100 ohms, 1/2W, 1%	01097
R4, R8	Resistor, 4.7K, 1/2W, 5%	00173
R5	Potentiometer, 100K	00634
R9	Potentiometer, 50K	01356
R10	Potentiometer, 1 meg	00640
R12	Resistor, 1K, 1/2W, 1%	01112
R13	Resistor, 1.2K, 1/2W, 5%	00110
R14	Resistor, 102 ohms, 1/2W, 1%	01102
R15, R20	Resistor, 85.8 ohms, 1/2W, 1%	00544
R16, R21	Resistor, 447 ohms, 1/2W, 1%	00605
R17, R22	Resistor, 944 ohms, 1/2W, 1%	00560
R18	Resistor, 19K, 1/2W, 1%	01250
R19	Resistor, 180K, 1/2W, 1%	01244
R23	Resistor, 250 ohms, 1/2W, 1%	00515
R24	Resistor, 200K, 1/2W, 1%	00477
R25	Resistor, 470K, 1/2W, 5%	00288

GP-4 PARTS LIST (Cont.)

Ref. Number	Part Name and Description	B/A No.
R26	Resistor, 6.8K, 1/2W, 5%	00378
R27	Resistor, 1.5K, 1/2W, 5%	00113
R28, R29	Resistor, 7.5K, 1/2W, 1%	00512
S1	Switch, rotary	00373
S2	Switch, lever	00379
S3	Switch, rotary	00377
S4	Switch, lever	00375
S5	Switch, rotary	09614
S6, S7, S9, S10	Switch, lever	00384
S8, S11	Switch, lever	00381
S12	Switch, toggle, SPDT	01358
M1	Meter	00970

GP-4 SUBASSEMBLIES

*S5S Coefficient Selector Switch Assembly consisting of:
S5, R11, R12, C4, R24, R8, C3, R6, R7, C1, C2, R1, R4, R2, R3, R14, and switch shields.

*S6S I_e or I_b -- (1.0 ma to 5.0 ma) consisting of:
S6, R15, R16

*S7S I_e or I_b -- (50 ma to 500 ma) consisting of:
S7, R17, R28

*S8S V_e or V_b -- (1.0V to 10V) consisting of:
S8, R19, R18

*S9S I_c -- (1.0 ma to 5 ma) consisting of:
S9, R20, R21

*S10S I_c -- (50 ma to 500 ma) consisting of:
S10, R22, R29

*S11S V_c -- (10V to 50V) consisting of:
S11, R23

*For customer convenience and ease of installation, these switch subassemblies are supplied with pertinent components mounted and wired.

SECTION 6
MAINTENANCE

6-1. BATTERY REPLACEMENT

The emitter battery (three 45-volt batteries in series) should be replaced when it is no longer possible to set I_e to 1 ma with a (good) transistor in the socket and the I_e adjust control at its maximum setting.

The collector battery (single 45-volt battery) should be replaced when the bias meter reads 30 volts or less when the V_c adjust control is at its maximum setting and no transistor is in the socket.

CAUTION: Do not leave low or dead batteries in case, as a chemical action may damage the instrument.

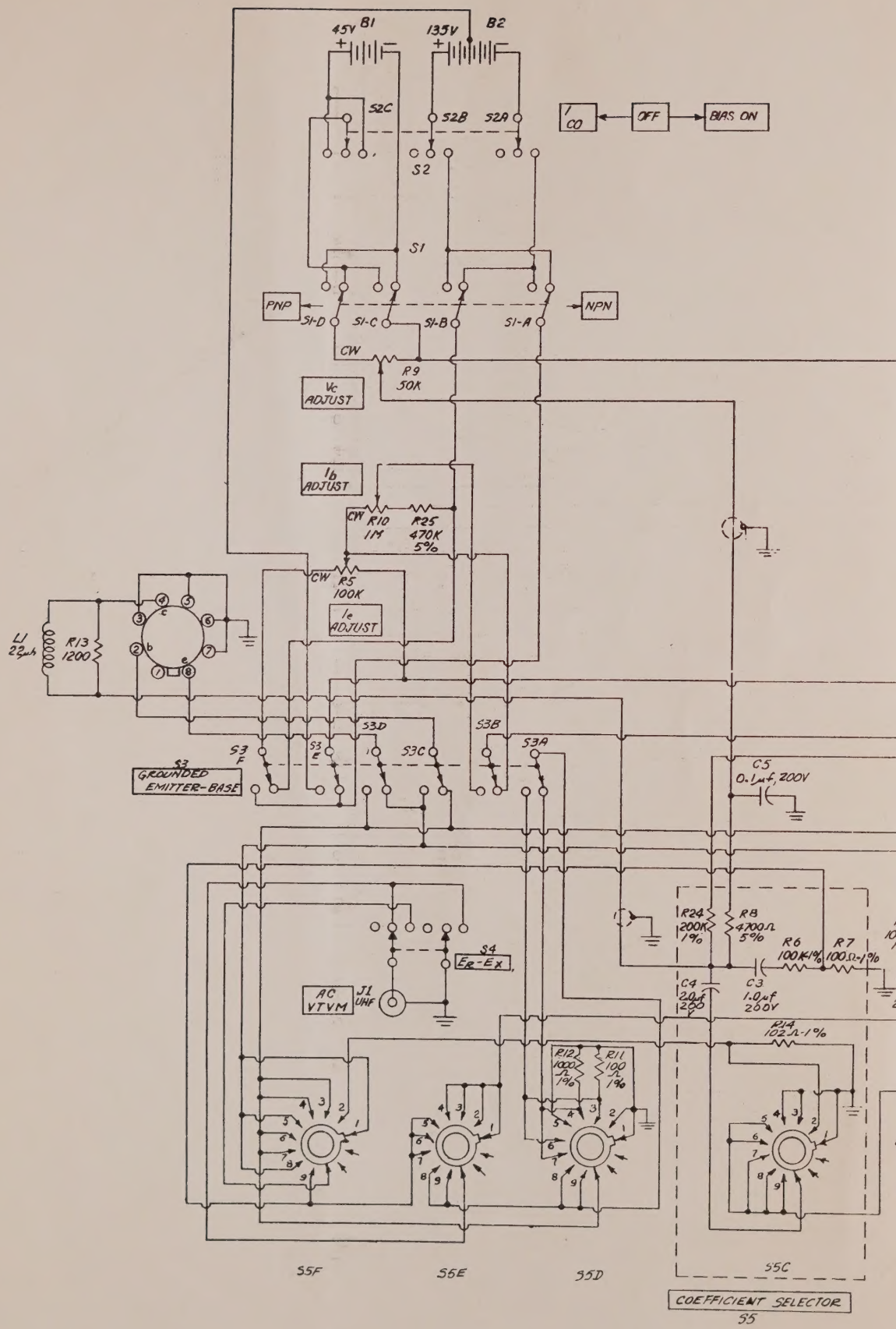
6-2. BATTERIES USED

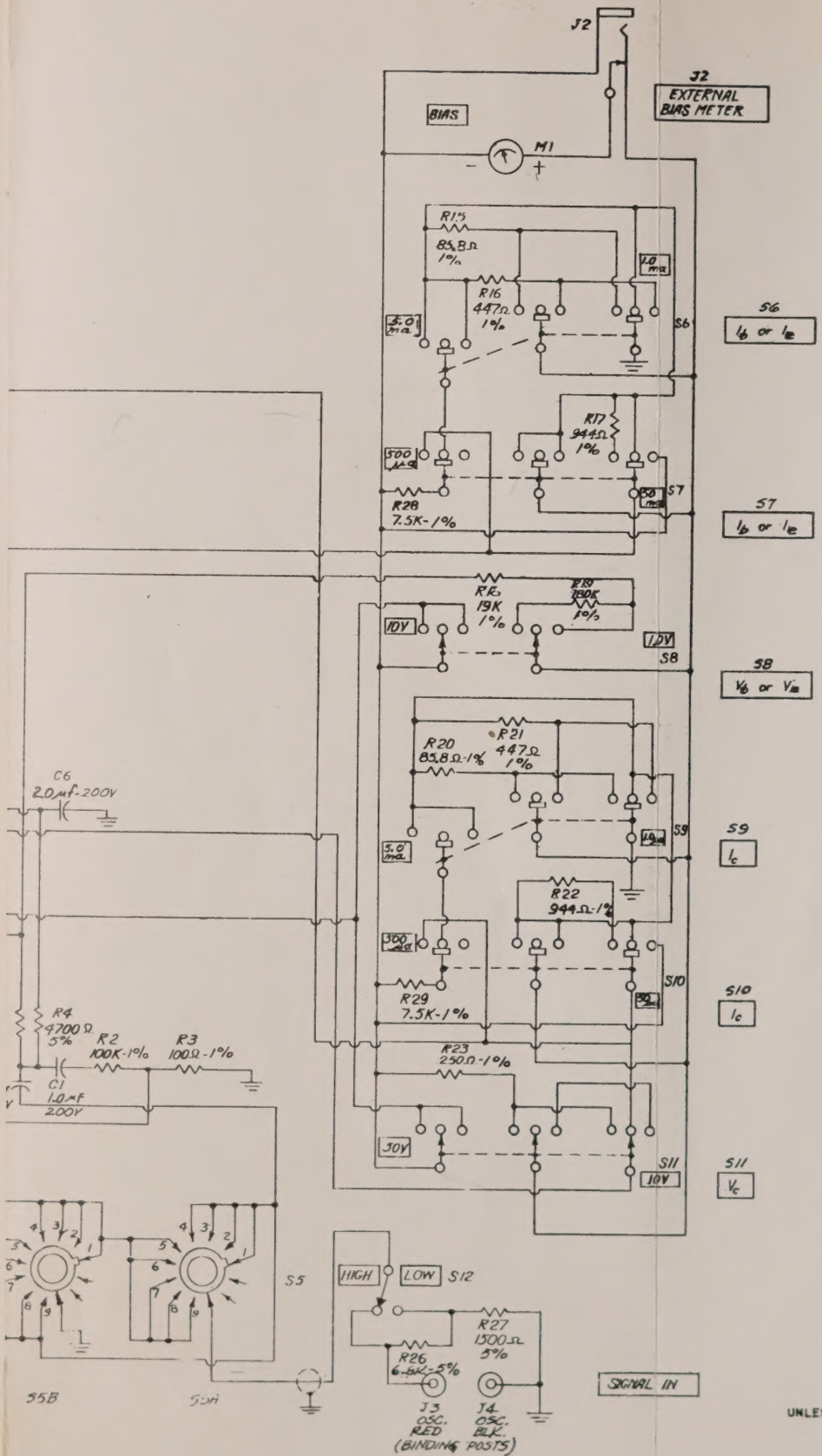
Burgess Type 5308 or equivalent.

Batteries are replaced in the Model GP-4 by removing the back panel of the cabinet.

In the Model GS-3, access to batteries is through a hinged door in the rear.

CAUTION: Be sure bias switch is OFF when removing batteries.


45V B1
135V B2
S2C
S2B
S2A
S2
S1
I CO
OFF
BIAS ON
PNP
S1-D
S1-C
S1-B
S1-A
NPN
CW
R9 50K
Vc ADJUST
Ib ADJUST
CW R10 1M
R25 470K 5%
CW R5 100K
Ie ADJUST
L1 22μh
R13 1200Ω
S3D
S3B
S3A
S3 F
S3 E
S3C
S3 GROUNDED EMITTER-BASE
C5 0.1μf, 200V
R24 200K 1%
R8 4700Ω 5%
R6 100K 1%
R7 100Ω 1%
C4 2.0μf 200
C3 1.0μf 200V
S4 Er-Ex
AC VTVM
J1 UHF
R14 102Ω 1%
R12 1000Ω 1%
R11 100Ω 1%
S5F
S5E
S5D
S5C
COEFFICIENT SELECTOR
S5



UNLESS NOTED ALL RESISTORS ARE 1/2WATT AND ± 5%

SCHEMATIC DIAGRAM
TRANSISTOR TEST SET MODELS
GS-3 & GP-4

REV.
C

WARRANTY

Baird-Atomic, Inc. (the "Company"), warrants this equipment for a period of 6 months from the date of shipment as follows: it warrants that all equipment of its manufacture is free from defects in material and workmanship at the time of shipment. If within 6 months of shipment any equipment of the Company's manufacture develops defects in material or workmanship under normal conditions of operation, the buyer of the equipment may return it to the Company within 30 days of such failure, for repairs at the expense of the Company excluding transportation costs, or in the case of any defective part may return such part to the Company which will repair or replace the same at its expense excluding transportation costs. A further warranty of 6 months on the same terms shall be applicable to any part so repaired or replaced. Except for Dekatron glow tubes, this warranty does not extend to stock components not manufactured by the Company.

The Company shall not be liable for damage or destruction of instruments during delivery or caused by other than employees of Baird-Atomic, Inc.; in any event, liability shall not exceed the cost of replacement of defective parts upon prompt notification of such defect. For return of equipment or any part thereof under the terms of the foregoing warranty a letter should be forwarded to Baird-Atomic, Inc., Attention: Sales Service Department, 33 University Road, Cambridge 38, Massachusetts. It should state owner's name and address; model and serial number of equipment; the order number under which it was purchased; the date of failure and a description of the circumstances surrounding same. Upon receipt of such information, shipping instructions for return of equipment or parts thereof will be forwarded promptly.